

# 4W High Power Laser Diode

## Description

The SLD343YT has a compatible package, and allows independent thermal and electric design.

It is a high power laser diode that affords easy optical design.

#### Features

- High-optical power output Recommended optical power output: Po = 4.0W
- High-optical power density: 4W/200µm

(Emitting line width)

## Applications

- Solid state laser excitation
- Medical use
- Material processing
- Measurement

#### Structure

AlGaAs quantum well structure laser diode

## **Operating Lifetime**

MTTF 10,000H (effective value) at Po = 4.0W, Tth =  $25^{\circ}C$ 

## Absolute Maximum Ratings (Tth = 25°C)

- Optical power output
  Po
  4.4
  W
  Reverse voltage
  VR
  LD
  2
  V
  PD
  15
  V
- Operating temperature (Tth) Topr -10 to +30 °C
- Storage temperature Tstg -40 to +85 °C

#### Warranty

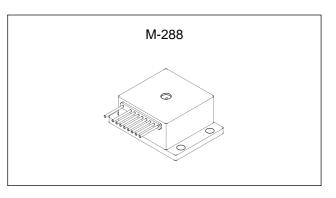
This warranty period shall be 90 days after receipt of the product or 1,000 hours operation time whichever is shorter.

Sony Quality Assurance Department shall analyze any product that fails during said warranty period, and if the analysis results show that the product failed due to material or manufacturing defects on the part of Sony, the product shall be replaced free of charge.

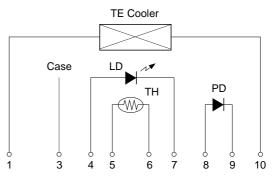
Laser diodes naturally have differing lifetimes which follow a Weibull distribution.

Special warranties are also available.

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## **Equivalent Circuit**



## Pin Configuration (Top View)

No.	Function		
1	TE cooler (negative)		
2	_		
3	Case		
4	Laser diode (anode)		
5	Thermistor		
6	Thermistor		
7	Laser diode (cathode)		
8	Photo diode (anode)		
9	Photo diode (cathode)		
10	TE cooler (positive)		

Electrical and optical	(101 - 11011113011011001010100, 101 - 200)						
Item		Symbol	Conditions	Min.	Тур.	Max.	Unit
Threshold current		lth			1.0	2.0	A
Operating current		Іор	Po = 4.0W		4.6	6.5	A
Operating voltage		Vop	Po = 4.0W		2.0	3.0	V
Wavelength*		λρ	Po = 4.0W	790		840	nm
Radiation angle	Perpendicular	θ⊥		10	23	35	degree
	Parallel	θ//	- Po = 4.0W	5	10	15	degree
Positional accuracy	Position	ΔΧ, ΔΥ				±100	μm
	Angle	$\Delta \phi \bot$	Po = 4.0W			±3	degree
		Δφ//				±4	degree
Differential efficiency		ησ	Po = 4.0W	0.5	1.1	1.5	W/A
Monitor current		Imon	Po = 4.0W VR = 10V	0.2	1.0	4.0	mA
Thermistor resistance		Rth	Tth = 25°C		10		kΩ

#### **Electrical and Optical Characteristics**

(Tth = Thermistor temperature, Tth = 25°C)

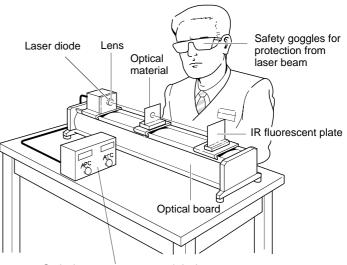
## \* Wavelength Selection Classification

Туре	Wavelength (nm)				
SLD343YT-1	795 ± 5				
SLD343YT-2	810 ± 10				
SLD343YT-3	830 ± 10				
Туре	Wavelength (nm)				
SLD343YT-21	798 ± 3				
SLD343YT-21 SLD343YT-24	798 ± 3 807 ± 3				

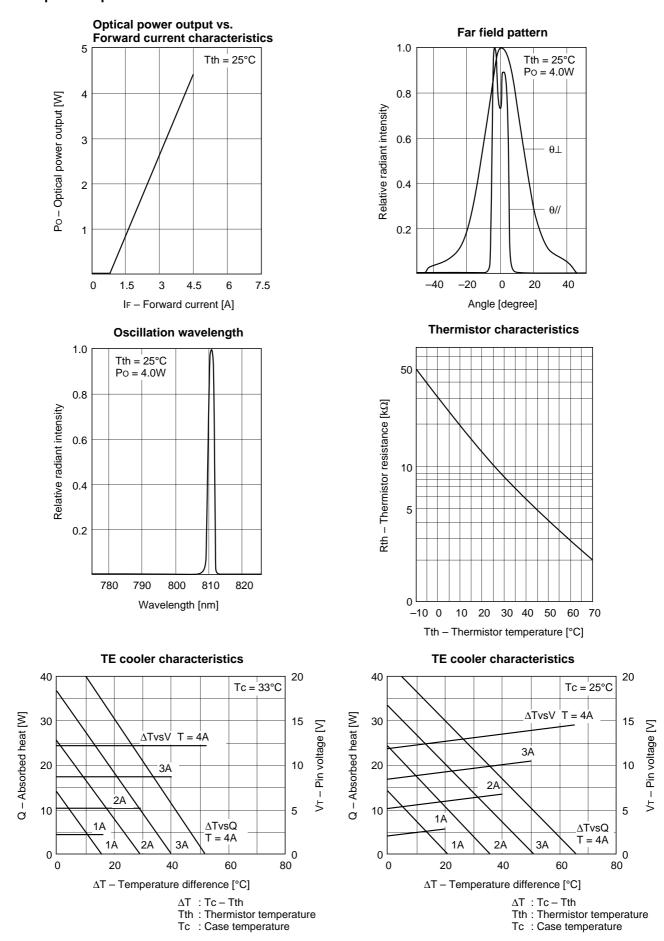
#### **Handling Precautions**

#### Eye protection against laser beams

The optical output of laser diodes ranges from several mW to 10W. However the optical power density of the laser beam at the diode chip reaches 1.5MW/cm<sup>2</sup>. Unlike gas lasers, since laser diode beams are divergent, uncollimated laser diode beams are fairly safe at a laser diode. For observing laser beams, ALWAYS use safety goggles that block infrared rays. Usage of IR scopes, IR cameras and fluorescent plates is also recommended for monitoring laser beams safely.

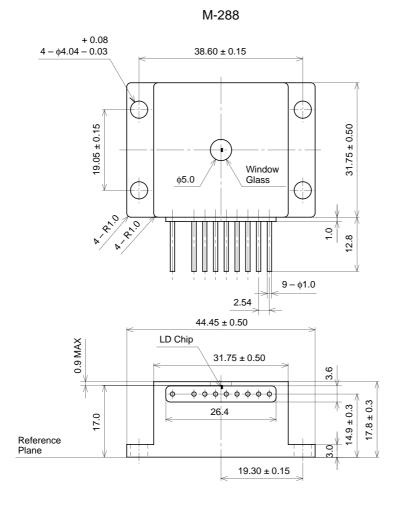


Optical power output control device Temperature control device



#### **Example of Representative Characteristics**

Package Outline Unit: mm



SONY CODE	M-288		
EIAJ CODE			
JEDEC CODE		PACKAGE MASS	150g